Traveling Wave
Parametric Amplifiers

(within DARTWARS)









Marco Faverzani University & INFN Milano - Bicocca



# Ultra low noise amplification for microwave readout: why?



### multiplexed readout of large detector/qubit array

N. Zobrist et al. <u>Appl. Phys. Lett. 115 (2019) 042601</u>
L. Ranzani et al. <u>Appl. Phys. Lett 113 (2018) 242602</u>
J. Heinsoo et al. <u>Phys. Rev. Applied 10 (2018) 034040</u>

### readout for axionic dark matter detection

C. Braggio et al. Rev. Sci. Instrum. 93 (2022) 094701

J.M. Navarro and B.K. Tan Proc. SPIE Int. Soc. Opt. Eng. 11881 (2021)

### microwave quantum key distribution

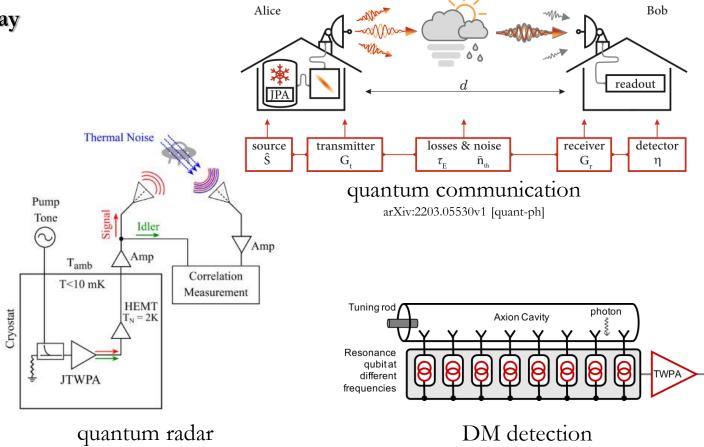
F. Fesquet et al. arXiv:2203.05530v1 [quant-ph]

### quantum radar

L. Fasolo et al. Measurement: Sensors 18 (2021) 100349

### squeezed-state microwave radiation source

A.L. Grimsmo and A. Blais Npj Quantum Inf. 3 (2017) 20 M. Esposito et al. Phys. Rev. Lett. 128 (2022) 153603

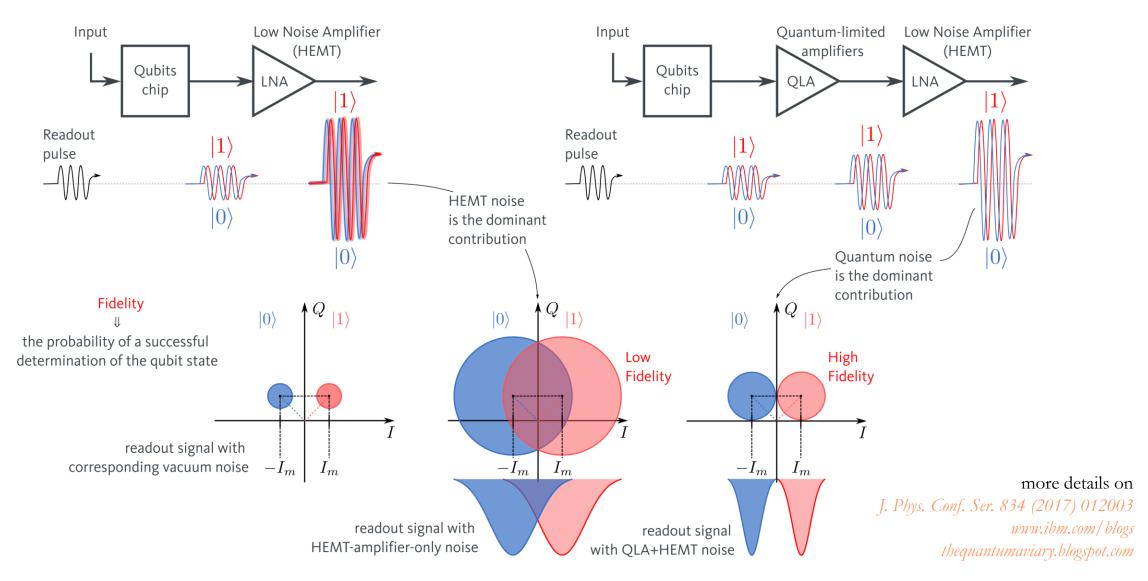


Measurement: Sensors 18 (2021) 100349 Proc.SPIE Int.Soc.Opt.Eng. 11881 (2021) 139-148

all these applications require broadband amplification and minimum added noise (i.e. information preservation)
Travelling-Wave Parametric Amplifiers (TWPA) are (near) quantum limit amplifiers capable to match these requirements

# High fidelity qubits readout



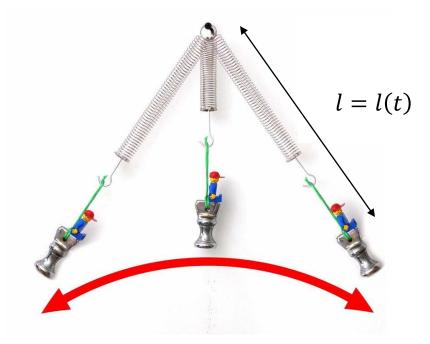




- 1) sinusoidal driving force  $(f_d = f_r \rightarrow \text{linear gain with time})$
- 2) one parameter periodically varied ( $f_d = 2f_r \rightarrow$  exponential growth)

e.g., the pendulum: 
$$\ddot{\theta}\cong \frac{g}{l}\theta$$
 ,  $\omega=\sqrt{g/l}$ 

if 
$$l = l(t) = l_0 \sin(2\omega t) \rightarrow \frac{dE(t)}{dt} \propto E(t)$$

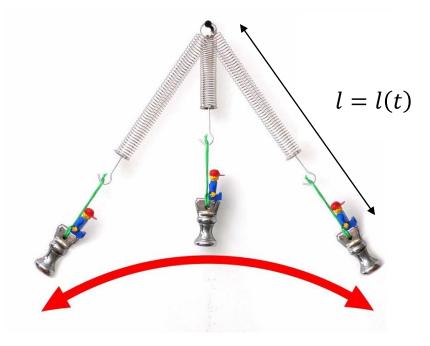


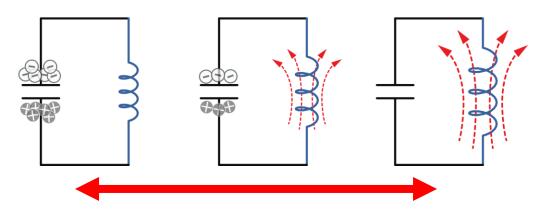


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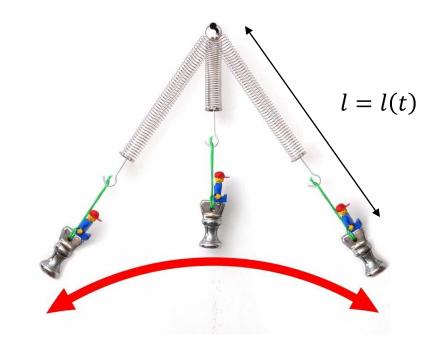


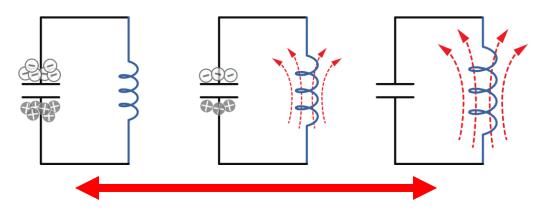


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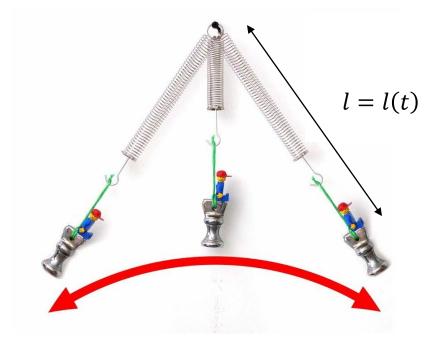
Josephson Junctions (JJ) 
$$\rightarrow$$
  $L_J = L_{J0} \frac{\arcsin(I/I_c)}{I/I_c}$ 

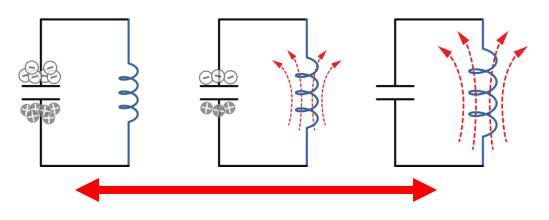


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if 
$$l = l(t) = l_0 \sin(2\omega t) \rightarrow \frac{dE(t)}{dt} \propto E(t)$$





Kinetic Inductance (KI) 
$$\rightarrow$$
  $L_K = L_{K0} \left( 1 + \frac{I^2}{I_*^2} \right)$ 

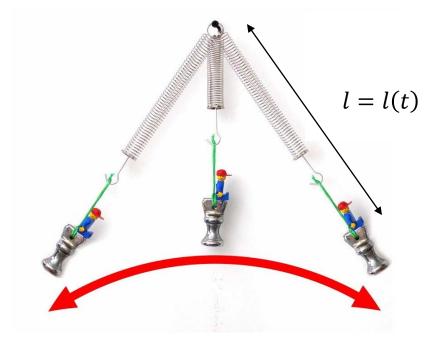


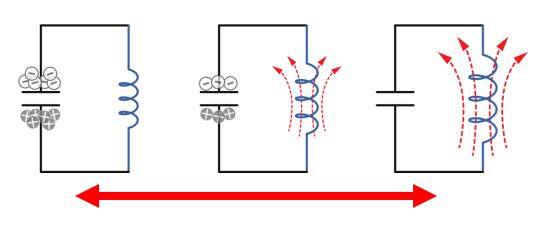
### Resonance if:

- 1) sinusoidal driving force  $(f_d = f_r \rightarrow \text{linear gain with time})$
- 2) one parameter periodically varied ( $f_d = 2f_r \rightarrow$  exponential growth)

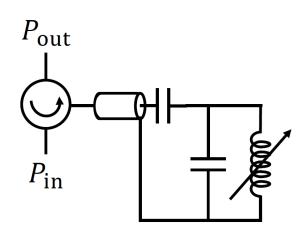
e.g., the pendulum: 
$$\ddot{\theta}\cong \frac{g}{l}\theta$$
 ,  $\omega=\sqrt{g/l}$ 

if 
$$l = l(t) = l_0 \sin(2\omega t) \rightarrow \frac{dE(t)}{dt} \propto E(t)$$





resonator-based parametric amplifiers (JPA, JPC, etc.)

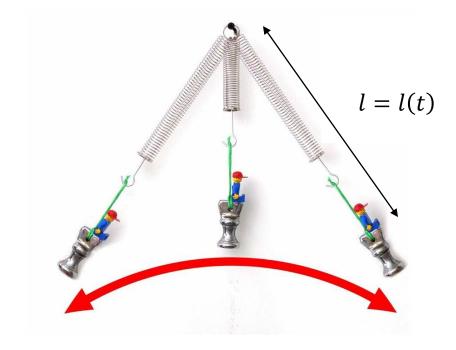


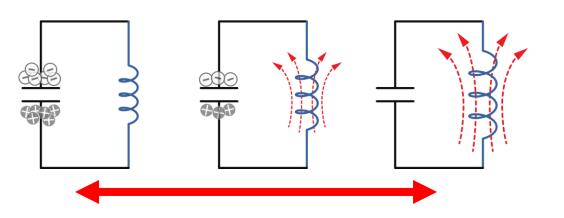


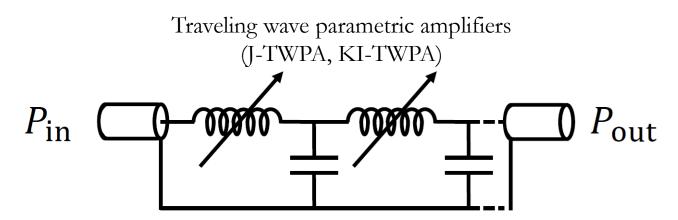
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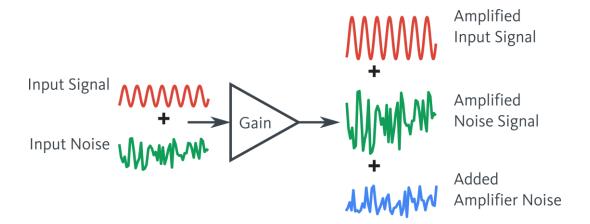




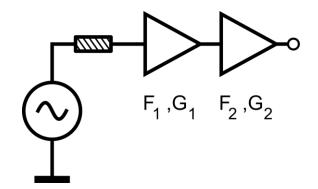


### Low noise readout





- the amplifier adds noise to several sources (thermal fluctuations, e-h recombination in semiconductors, etc.)
- a quantum limited amplifier has an added (temperature) noise  $T_N/f \sim b/2k_B \sim 25 \text{ mK/GHz}$
- in a two-stage amplification scheme, the first stage dominates the overall noise figure (if  $G_1\gg F_2$ )

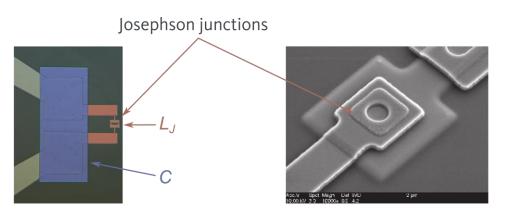


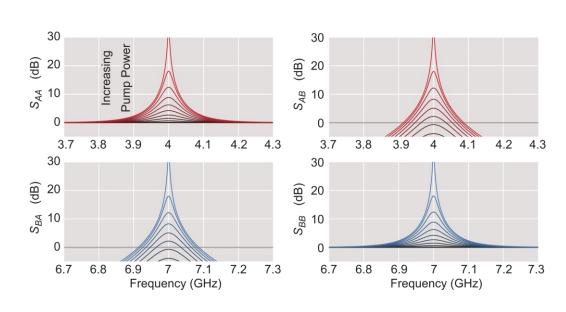
$$F_{TOT} = F_1 + \frac{F_2 - 1}{G_1}$$

# Josephson Parametric Amplifiers (JPA)



- signal to be amplified mixed with a strong pump through a nonlinear element
- in JPAs, non-linearity provided by the Josephson junction
- demonstrated noise level close to the quantum limit
- very narrow bandwidth < 100 MHz
  - > few detectors/qubits per line
  - > product gain-BW is fixed
- very small saturation power < -100 dBm
  - > few devices per line
- currently employed as a first stage of amplification in reading out superconducting qubits and RF cavities





IEEE Microwave Magazine 21, 8 (2020) 45

# Traveling Wave Parametric Amplifiers (TWPAs)



• transmission line with embedded non-linear elements

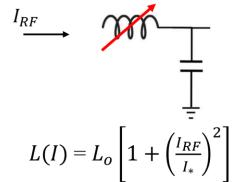
Phys. Rev. B 87, 144301

 non-linearity provided by Josephson Junction or intrinsic (non-linear) Kinetic Inductance of a superconductor

Unbiased transmission line: 4-wave mixing

$$\Delta \beta = k_s + k_i - 2k_n$$

$$2\omega_p = \omega_s + \omega_i$$

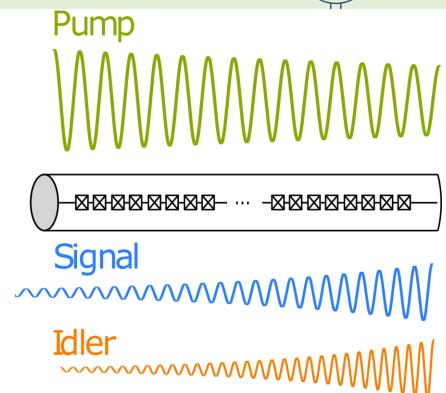


Biased transmission line: 3-wave mixing

$$\Delta\beta=k_s+k_i-k_p$$

$$\omega_p = \omega_s + \omega_i$$

$$L(I) \approx L_o \left[ 1 + \frac{I_{dc}^2}{I_*^2} + 2 \frac{I_{RF}I_{dc}}{I_*^2} \right]$$



A large pump tone  $(f_p)$  modulates the inductance, coupling the pump to a signal (and an idler) tone via frequency mixing

# Periodic loading

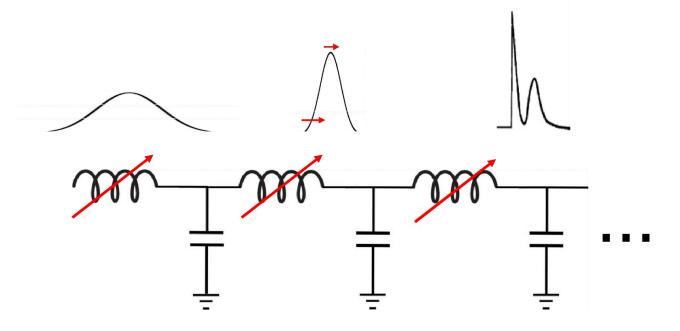


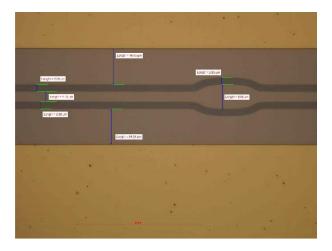
• periodic loading along the transmission line creates the phase matching condition

$$\Delta \beta = k_s + k_i - k_p = -\frac{k_p |A_p|^2}{I_*'^2}$$

- prevents creation of shock waves
  - velocity decreases with current
  - tail of a pulse moves faster than peak
  - shock waves would limit the gain at 3 dB!
- avoids coupling with higher harmonics of the pump
- ➤ High (exponential) gain:

$$G = \frac{1}{4} \exp(2 \frac{k_p |A_p|^2}{I_*'^2})$$

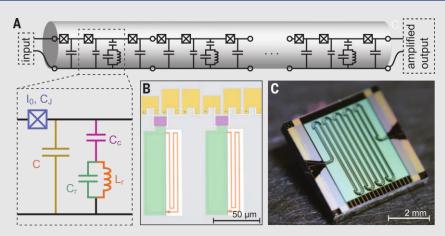




### TWPAs: Josephson and Kinetic Inductance



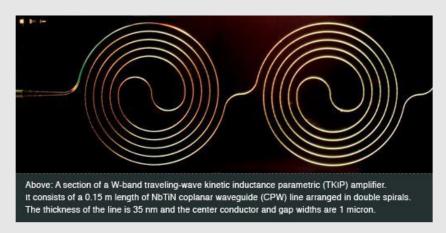
### Traveling Wave Josephson Parametric Amplifiers



Science 350, 6258 (2015) 307-310

- TWJPAs: non-linear lumped element transmission line
- one single cell consists of a Josephson Junction plus a capacitive shunt toward the ground
- demonstrated quantum-limited noise level
- wide BW > 4 GHz @ 5 GHz
- limited gain < 20 dB
- small saturation power < -90 dBm

### Kinetic Inductance Traveling Wave Parametric Amplifiers



Nature Physics 8 (2012) 623–627

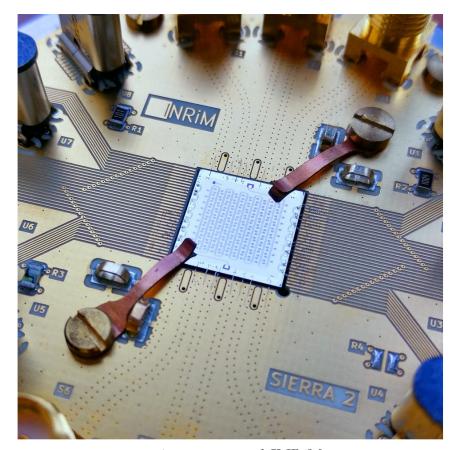
- KI-TWPA (a.k.a. KIT): distributed non-linear kinetic inductance of TiN or NbTiN
- patterned into CPW or lumped element artificial transmission line
- noise close to quantum limit
- wide BW >4 GHz @ 5 GHz
- limited gain and gain profile with large ripple
- high saturation power: from -50 to -45 dBm

### DARTWARS: Detector Array Readout with Traveling Wave AmplifieRS



### The main aims of DARTWARS are:

- 1. development of high-performance amplifiers both KIT and TWJPA optimizing design, new materials and fabrication processes
  - high gain  $\sim 20 \text{ dB}$
  - large saturation power  $\sim 50 \text{ dBm}$
  - (nearly) quantum limited noise  $T_N \le 600 \text{ mK}$
  - reduced gain ripple
  - yield improvement
- 2. demonstration of readout of various detectors/devices (i.e., TESs, MKIDs, RF cavities and qubits) with improved performances thanks to the amplification with added noise at the quantum level



picture courtesy of INRiM

### DARTWARS: the collaboration

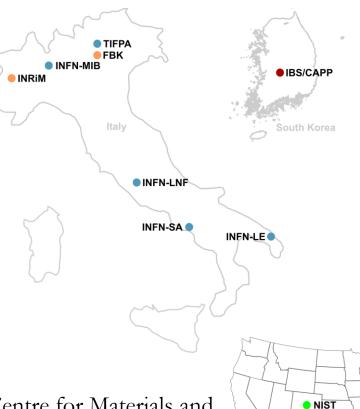


### **INFN** units:

- MIB: coordination of the whole project with a focus on the design and characterization of the devices (mainly DTWKI)
- LNF COLD (CryOgenic Laboratory for Detectors): supervision of the devices' fabrication and participation in the characterization (mainly TWJPA)
- LE: investigation of magnon-cavity polaritons applied to quantum computing and quantum sensing
- SA: coordination of design and simulation of TWPAs; packaging and testing of TWJPA
- TIFPA: supervision of production at FBK; participation in the characterization (mainly DTWKI)

### Other institutions:

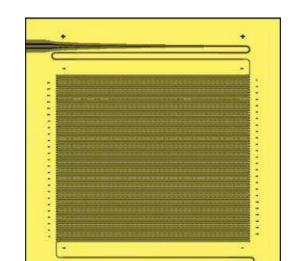
- Fondazione Bruno Kessler (FBK) Micro System Technology group (MST) of Centre for Materials and Microsystems (CMM): fabrication of DTWKI prototypes
- Istituto Nazionale di Ricerca Metrologica (INRiM): design and fabrication of TWJPA prototypes
- Institute for Basic Science Center for Axion and Precision Physics Research (IBS-CAPP): co-finances the production; participation in the characterization
- National Institute of Standards and Technology (NIST): participation in designing and testing of DTWKI



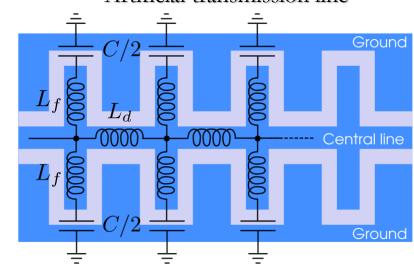
### KITWPA within DARTWARS



### **CPW**



Artificial transmission line



### • CPW:

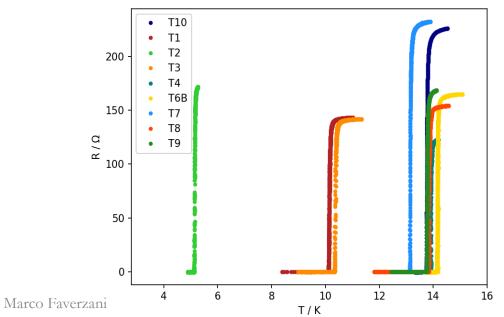
- ➤ first implementation of KI-TWPA
- B. Eom et. al., Nature Phys. 8 (2012) 623–627

- > ease of fabrication
- ➤ good gains, BW and noise
- ➤ 2 m long CPW for +15 dB gain
- $\triangleright$  high impedance (200  $\Omega$ )  $\rightarrow$  match to 50  $\Omega$  required
- Artificial transmission line:
  - > small sections of a CPW recreate a transmission line of lumped-elements
  - ➤ 20 cm long transmission line for +15 dB gain
  - ➤ near-quantum-limited noise demonstrated in the 3.5-5.5 GHz

M. Malnou et al., PRX Quantum 2 (2021) 010302

DART WARS

- Goal: 20 nm thick NbTiN film  $T_c \sim 14$ K,  $L_k \sim 10$  pH/ $\square$
- new sputter (PVD Kenosistec 800 Cluster)
- sputter target Nb<sub>0.80</sub>Ti<sub>0.20</sub>
- Nb dry etch with SF<sub>6</sub> and Ar (new recipe)
- how do  $(T_c, R_s, L_k)$  depend on sputtering parameters?





W	P [W]	p [mbar]	$f_{\rm N2}$ [sccm]
T1	700	2e-3	5
Т2	700	3e-3	4
Т3	700	3e-3	5
T4	700	3e-3	6
Т5	1200	3e-3	5
Т6	700	3e-3	7
Т6В	700	3e-3	7
Т7	700	3e-3	8
Т8	700	3e-3	6.5
Т9	700	3e-3	7
T10	600	3e-3	7

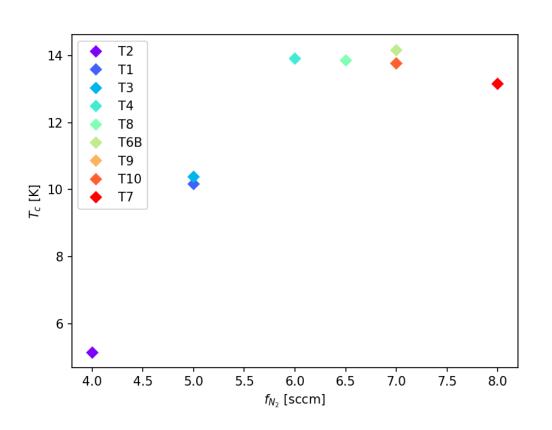
For all wafers:

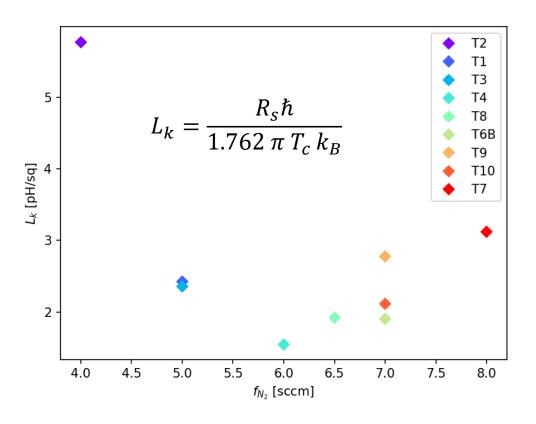
Ar flow = 50 sccm t = 6 minutes T = 400 °C

13



### Run DWT2





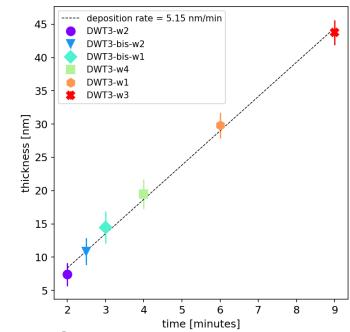


### Run DWT3

Wafer	t [minutes]
DWT3/w1	6
DWT3/w2	2
DWT3/w3	9
DWT3/w4	4
DWT3-bis/w1	3
DWT3-bis/w2	2.5

For all wafers:

$$P = 600 \text{ W}$$
  
 $p = 3\text{e}-3 \text{ mbar}$   
Ar flux = 50 sccm  
 $N_2 \text{ flux} = 7 \text{ sccm}$   
 $T = 400 \text{ °C}$ 

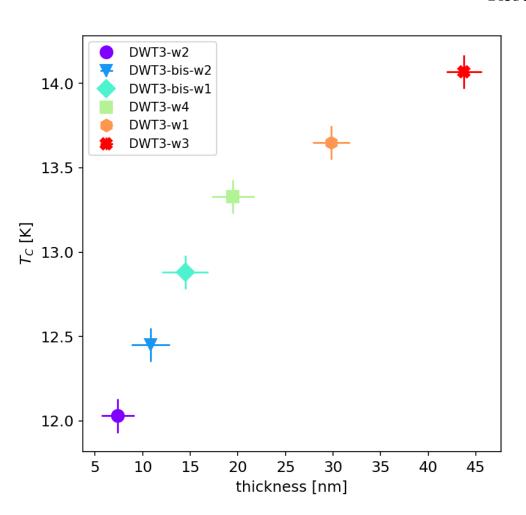


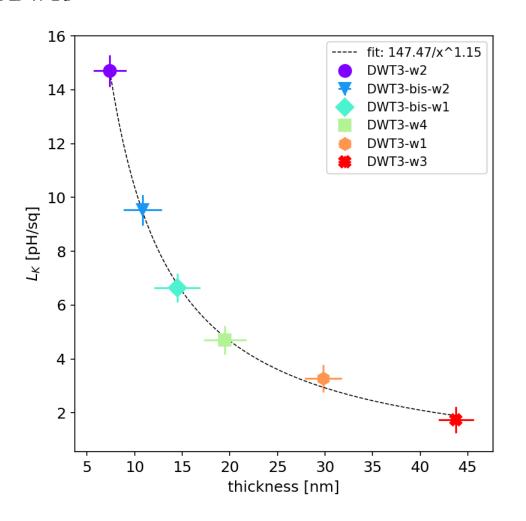
Lithography with KIDs mask → more precise measurement of thickness:





### Results on Run DWT3

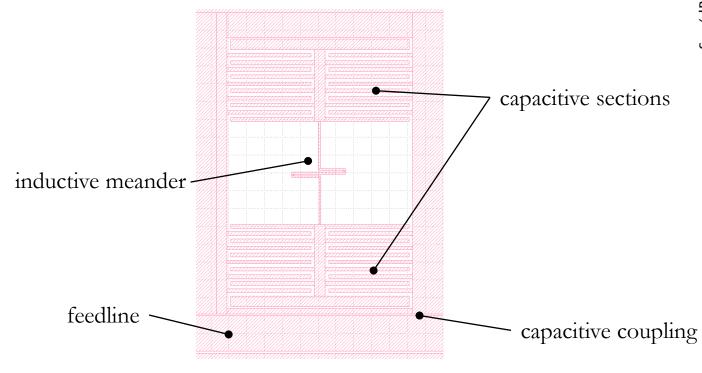




# KITWPA: material characterization @FBK/TIFPA



NbTiN patterned into micro-resonators (KIDs) to characterize the kinetic inductance (and its non-linearity)



Device from film W6 -30 -35 Frequency (GHz) (dB) 4.557e+09 4.558e+09 4.556e+09 4.559e+09 4.56e+09 Frequency (GHz)

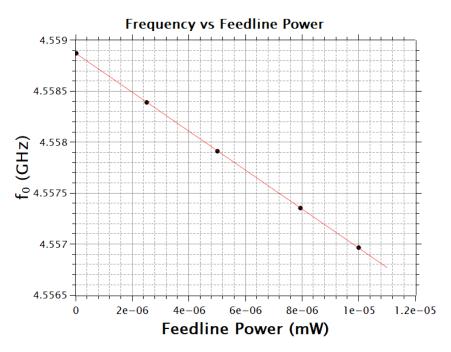
Quality factors in the range  $(0.2 - 1) \cdot 10^5$ 

$$L_k = L_{k_0} \left[ 1 + \left( \frac{I}{I_*} \right)^2 \right]$$

# KITWPA: material characterization @FBK/TIFPA (cont'd)



M. Borghesi et. al., arXiv:2208.10101 [quant-ph]

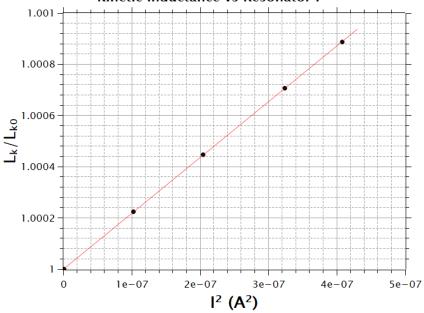


need to:

- relate  $L_k$  to  $f_{res} \rightarrow$  Sonnet simulation:  $(f_{res})^{-2} \propto (L_k + L_g)C$
- relate  $I^2$  to  $P_{\text{feedline}} \rightarrow \text{estimated } C \text{ and } L \text{ from Sonnet}$ → circuit simulator (QUCS)
- estimate  $I_*$  from  $L_k(f_{res})$  (Sonnet)

$$L_k = L_{k_0} \left[ 1 + \left( \frac{I}{I_*} \right)^2 \right]$$

Kinetic Inductance vs Resonator I2

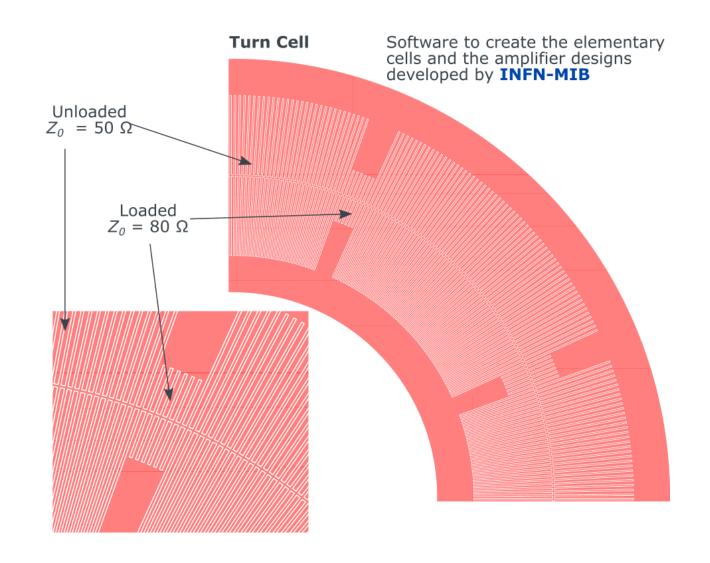


 $L_{\rm s}$  measured between ~ 4 and 50 pH/sq  $I_*$  (18 – 20) mA  $I_{\rm c}$  (2.2 – 2.4) mA

# KITWPA – Design

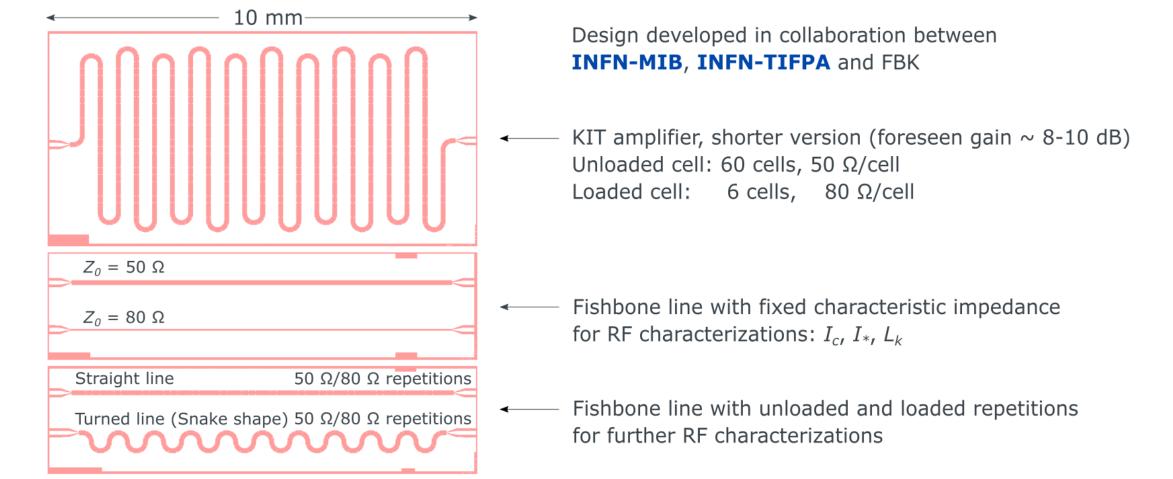


# **Straight Cell** Unloaded Loaded Unloaded $Z_0 = 50 \Omega Z_0 = 80 \Omega Z_0 = 50 \Omega$



# KITWPA – Design

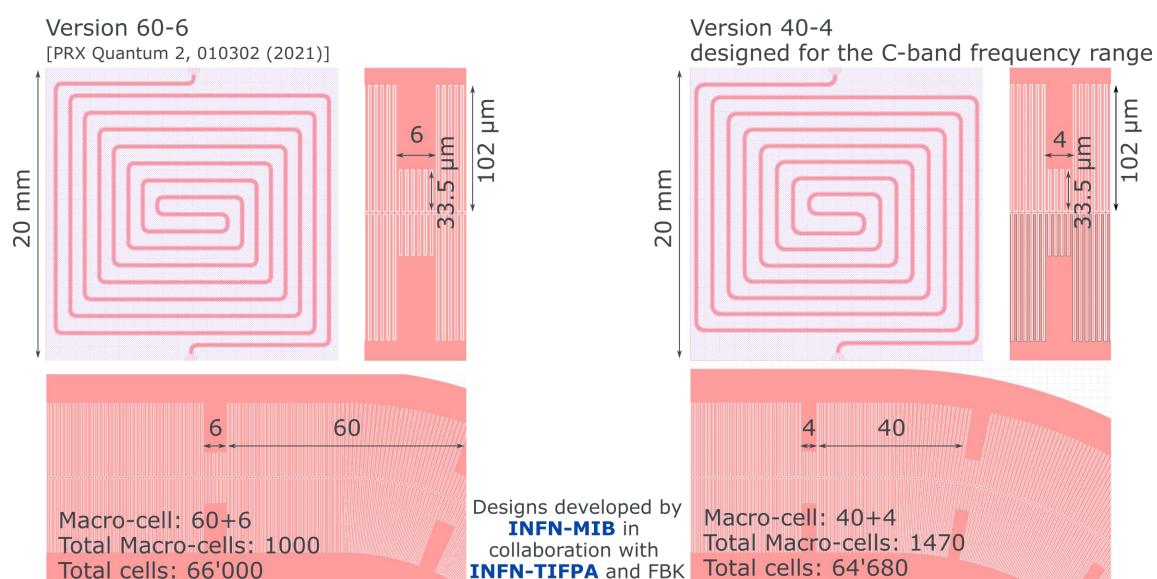




Wires with different size for DC characterizations:  $T_c$ ,  $R_n$ ,  $L_k$ 

### KITWPA – Design



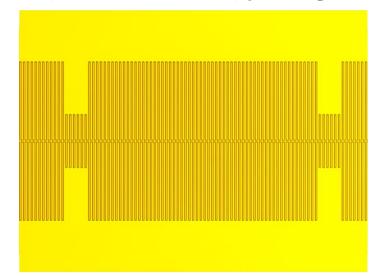


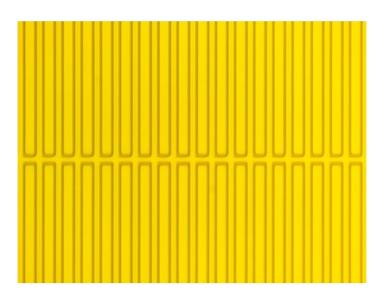
INFN-TIFPA and FBK

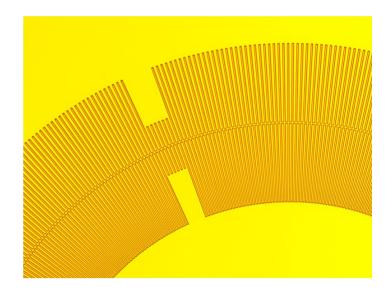
### KITWPA – Production

# DART WARS

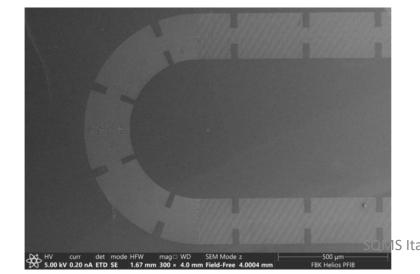
### Optical Microscopy Images

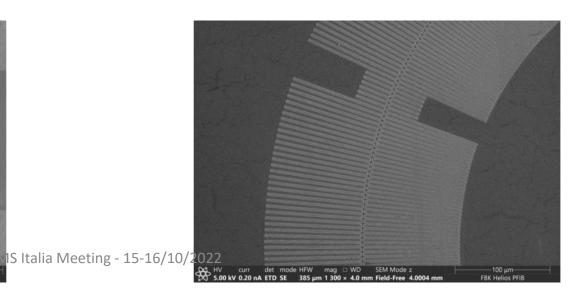






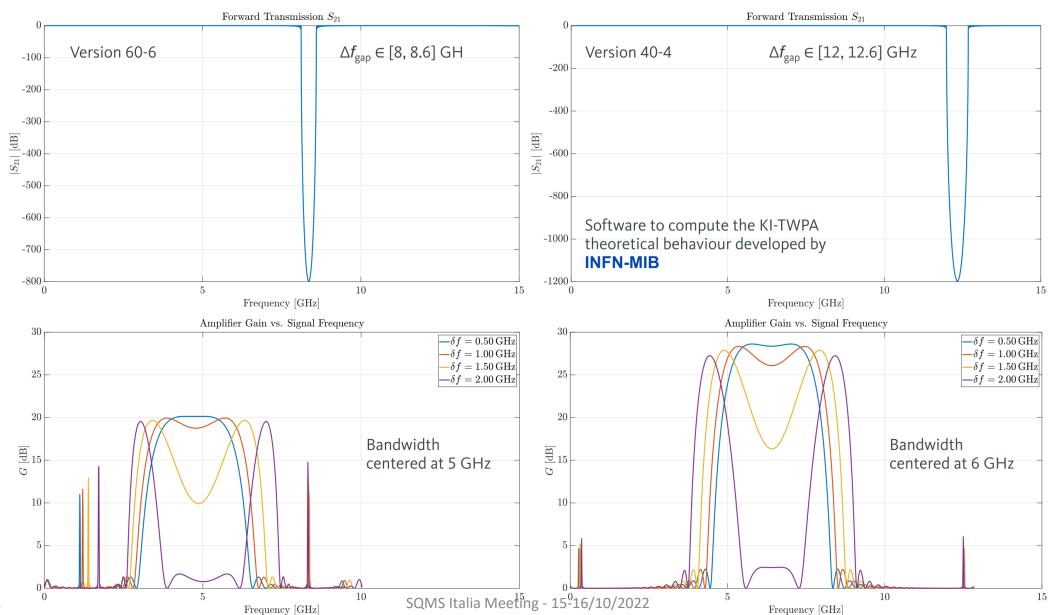
Scanning Electron Microscopy Images





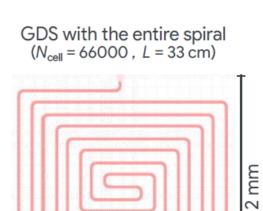
# KITWPA – Expected performance

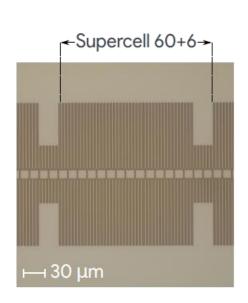


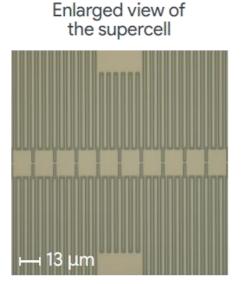


# KITWPA @NIST









Supercell in a curved part

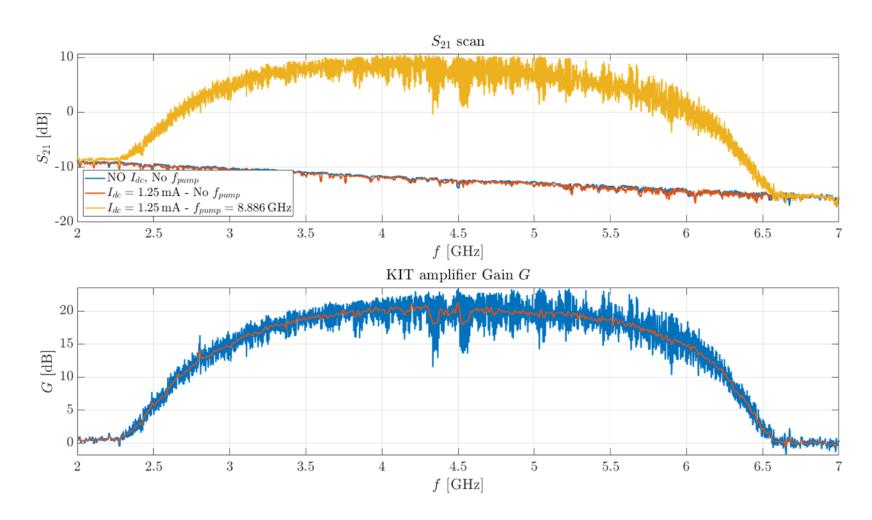
• NbTiN thickness 20

- first KI-TWPA prototypes with t = 10 nm produced at the end of October with two different unloaded/loaded cell repetition (60-6 and 42-6 for two different frequency range)
- characterization measurements in progress

# KITWPA @NIST



### Device characterization – NbTiN 20 nm



# KITWPA @NIST



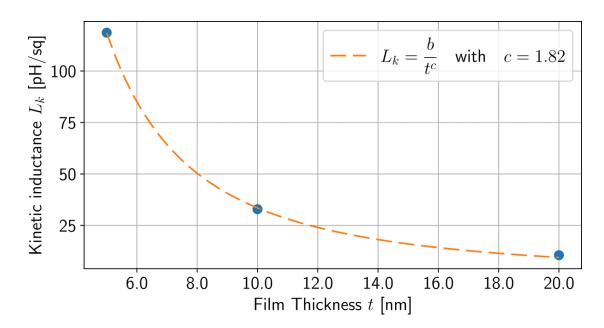
• want to reduce thickness of film

$$L(I) = L_0(1 + \frac{I^2}{I_*^2})$$

- smaller thickness  $\rightarrow$  larger  $L_0 \rightarrow$  lower I to get same L
- smaller power, meaning lower added noise

Normalized Transition Curve						
1.0						
1.0 -						
- 8.0 Su			Comment			
$R/R_{ m Sn}$			3890000000			
			00000		O	$t=5\mathrm{nm}$
0.2 -		(C)	000000000000000000000000000000000000000		0	$t = 10 \mathrm{nm}$ $t = 20 \mathrm{nm}$
0.0		0 1	2	1.4		
10 12 14 16 Temperature [K]						

t [nm]	Т <sub>с</sub> [K]	$L^0_{ m k}$ [pH/ $\square$ ]	$L^{\mathrm{res}}_{}\mathbf{k}}$ [pH/ $\square$ ]	$\mathcal{Q}_{\mathrm{i}}$
5	9.5	118.6	93.3	30k
10	11.6	32.9	31.5	50k
20	13.1	10.5	10.6	70k

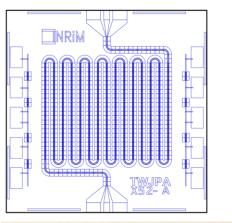


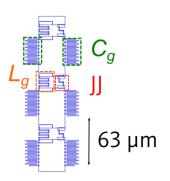
### TWJPA within DARTWARS



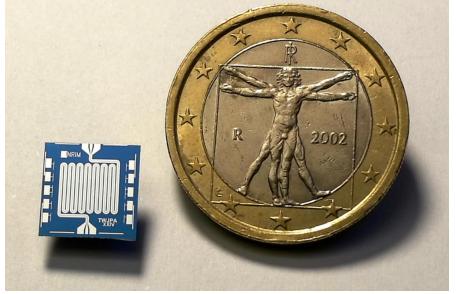
- recent studies suggest that TWJPA operated in the three-wave mixing (3WM) mode might increase the power handling, while decreasing the gain vs. frequency ripple
- new design 3WM TWJPA based on microwave transmission line composed of a serial array of non-hysteretic one-junction rf-SQUIDs
- mixing process due to the non-linear inductance of the JJs
- JJs created as Al/Al-Ox/Al tri-layer exploiting the Niemeyer-Dolan technique
- design and production made in collaboration with the Istituto Nazionale di Ricerca Metrologica (INRiM, Torino)

### TWJPA chip fabricated at INRiM



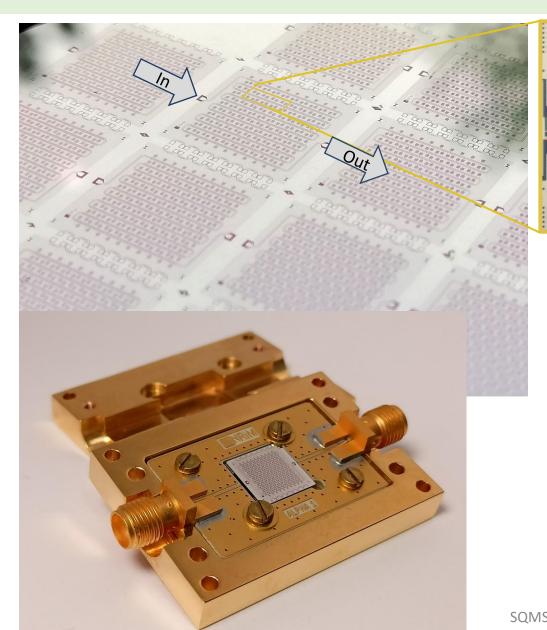


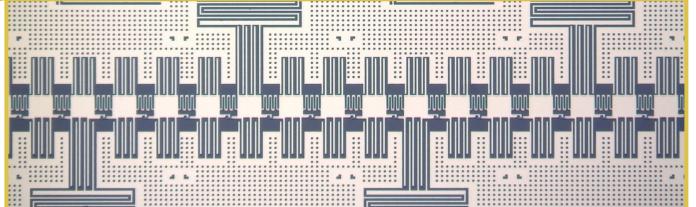
3 elementary cells



# JTWPA







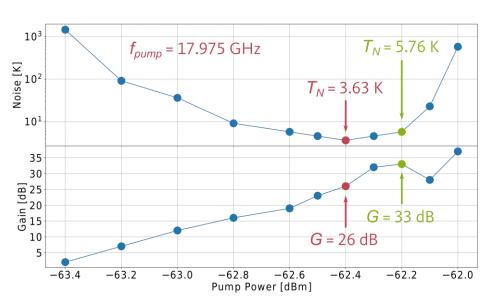
- Josephson Junction **spread** of parameters deeply affect the amplifiers performances (eg. gain)
- Due to the exponential dependence of its properties, Josephson tunnel junctions are the **bottleneck** of the whole JTWPAs operation

### TWJPA within DARTWARS



- chips with TWJPA produced at INRiM were tested both at LNF and IBS-CAPP
- measurements showed parametric amplification but with a non-homogeneous behavior in frequency: non-homogeneous fabrication of the  $\sim 900$  JJs of the device
- gain up to 30 dB was observed at particular frequencies and with a minimum noise temperature of 3.63 K
- new design with modified dispersion relation to reducing mismatch between the traveling tones, is in development
- production and characterization of JJs @ INRiM and MIB

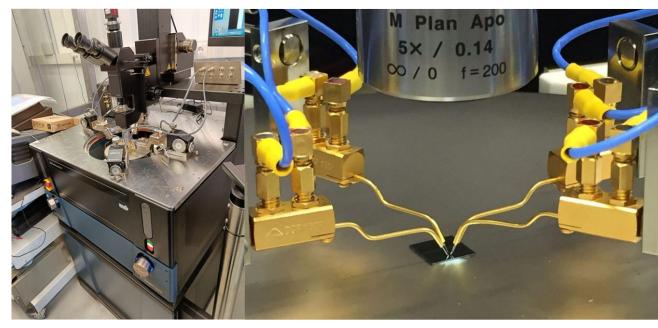




# JJs production and characterization @INRiM and MIB



- JJs produced at INRiM with two oxidation processes (dynamic and static), but with fixed *time* × *pressure*<sup>0.5</sup>
- JJs designed to have a  $I_c = 4 \mu A$
- expected normal resistance (from Ambegaokar-Baratoff) is  $R_{\rm N} \approx 80~\Omega$
- normal resistance measured with 4-terminal probe station coupled to a Keithley 4200A Parameter Analyzer (current ramp  $0.1 \div 10~\mu\text{A}$ )
- on average  $R_N$  is close to the target value
  - still to address spread in value (around 15%)





### Conclusions



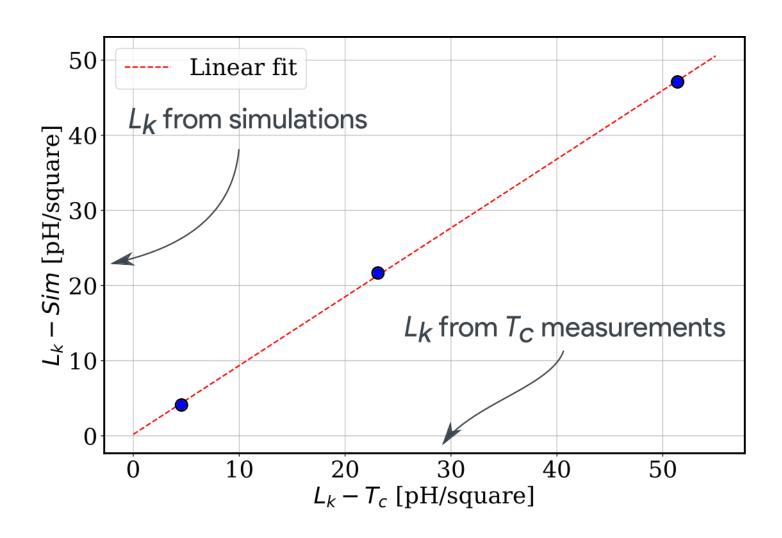
- the demand for high gain/wide bandwidth with low noise amplifiers is driven by the readout of superconducting qubits, cryo detectors, RF cavities, ...
- design of DARTWARS KI-TWPA started in 2021 and the first material characterizations have been performed across 2021 and 2022. The first devices has been produced during summer; next production with new target expected soon
- demonstration of detectors/qubits readout is expected for 2023
- DARTWARS will allow to build the expertise within INFN in designing and developing innovative quantum devices
- the results of DARTWARS will potentially impact particle/astro-physics (such as  $m_v$  measurement, dark matter,  $0\nu\beta\beta$ , coherent elastic neutrino-nucleus scattering, ...) as much as fast-growing fields such as quantum computing/sensing, quantum squeezing, quantum radar, ...
- more details available at <a href="https://dartwars.unimib.it/">https://dartwars.unimib.it/</a> and <a href="https://biqute.unimib.it/">https://biqute.unimib.it/</a>

# Backup slides



# $L_{\rm s}$ comparison

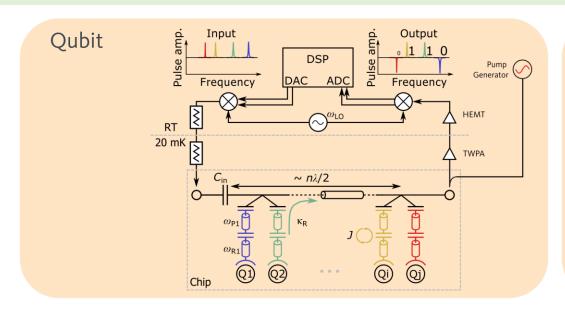


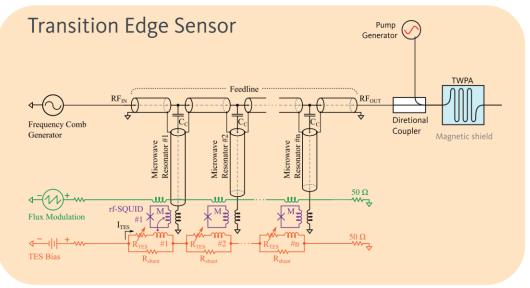


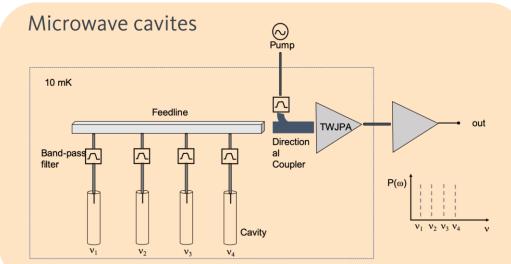
# DARTWARS: readout of superconducting devices

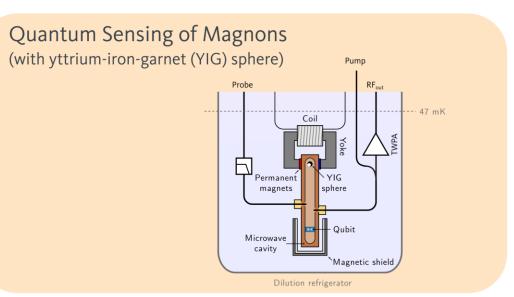


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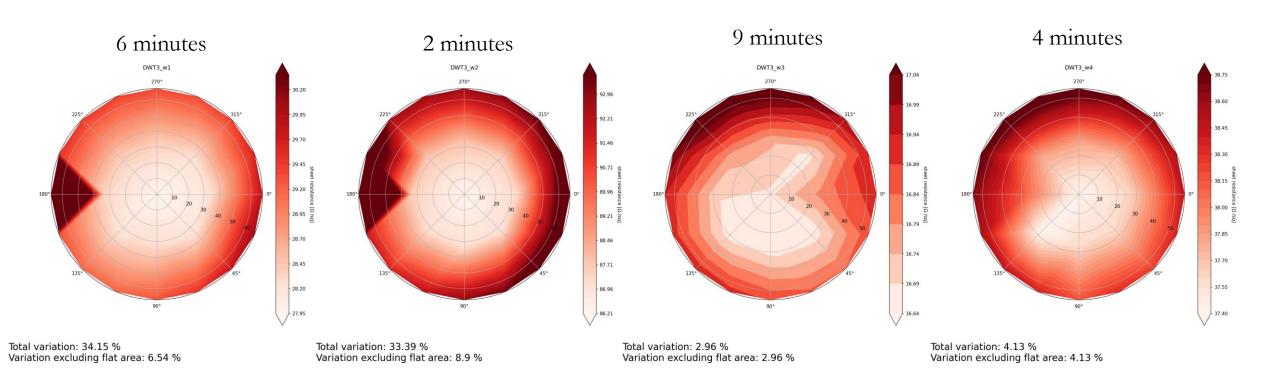








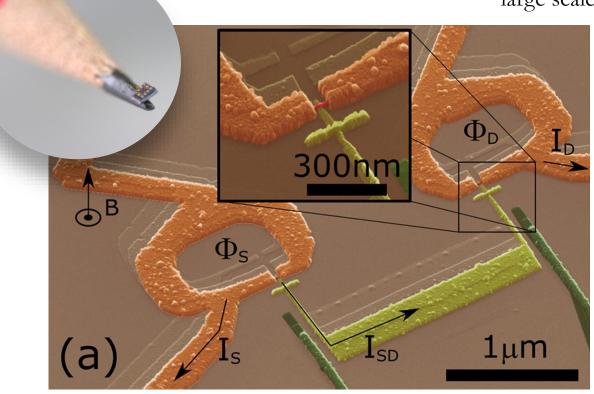
### homogeneity test from sheet resistance measurement



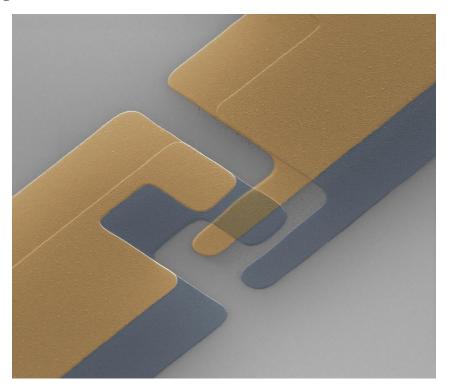
# JTWPA – Technological challenge



Need for **reproducibility** and **stability** of Josephson Junctions on a large scale approach



E. Enrico, et al., Single charge transport in a fully superconducting SQUISET locally tuned by self-inductance effects, AIP Advances **12**, 055122 (2022)



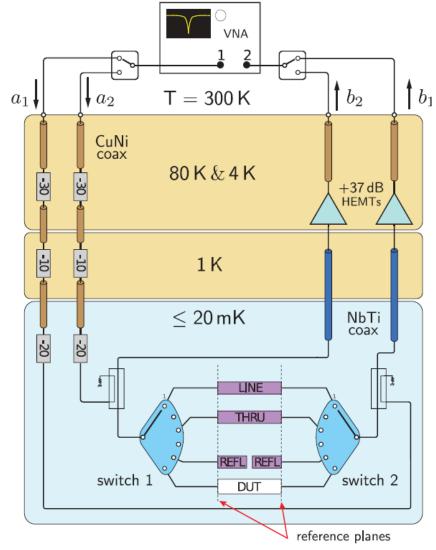
UV shadow lithography based Josephson Junction

# Cryogenic Thru-Reflect-Line (TRL)



- necessary to precisely evaluate the *S*-parameters of the device excluding the effects of the readout line
- of great importance for DARTWARS, it will be developed in collaboration with the INRiM branch of SuperQuant (20FUN07 SUPERQUANT - Microwave Metrology for Superconducting Quantum Circuits, under the European Metrology Programme for Innovation and Research (EMPIR))
- technique of great utility also in the field of material characterization finalized to quantum computing

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